

Features

- ✧ Glass passivated chip junction
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode



Mechanical Data

- ✧ Case: TO-220AB Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering guaranteed: 260°C/10s/.16", (4.06mm) from case
- ✧ Weight: 2.24 grams

Ordering Information(example)

Part No.	Package	Packing	Packing code	Packing code (Green)
HER1001G	TO-220AB	50 / TUBE	C0	C0G

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	HER 1001G	HER 1002G	HER 1003G	HER 1004G	HER 1005G	HER 1006G	HER 1007G	HER 1008G	Units	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V	
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V	
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V	
Maximum Average Forward Rectified Current	$I_{F(AV)}$	10								A	
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	125								A	
Maximum Instantaneous Forward Voltage (Note 1) @ 5 A	V_F	1.0			1.3		1.7			V	
Maximum DC Reverse Current @ $T_A=25\text{ }^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A=125\text{ }^\circ\text{C}$	I_R	10					400				uA uA
Maximum Reverse Recovery Time (Note 2)	T_{rr}	50					80				nS
Typical Junction Capacitance (Note 3)	C_j	60					40				pF
Typical Thermal Resistance	$R_{\theta JC}$	1.5								$^\circ\text{C/W}$	
Operating Temperature Range	T_J	- 55 to + 150								$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	- 55 to + 150								$^\circ\text{C}$	

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $IRR=0.25A$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (HER1001G THRU HER1008G)

FIG. 1- MAXIMUM FORWARD CURRENT DERATING CURVE

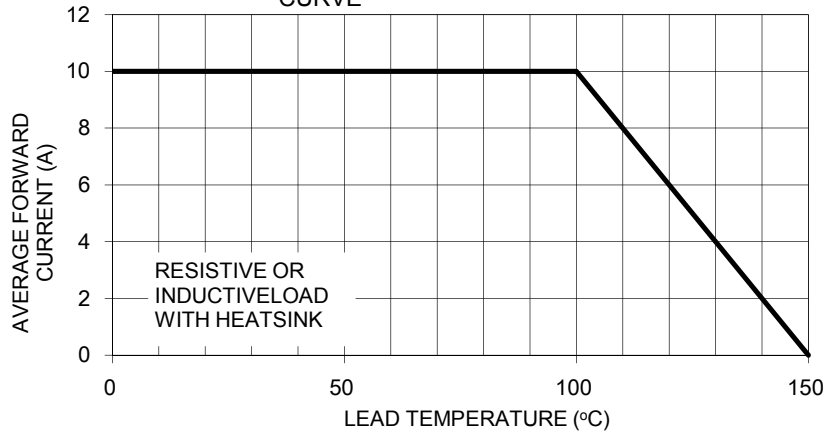


FIG. 2- TYPICAL REVERSE CHARACTERISTICS

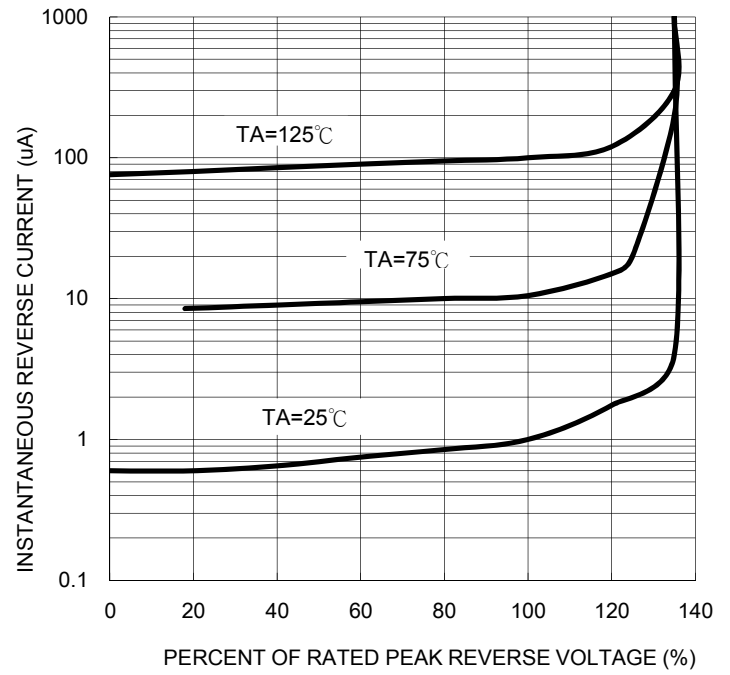


FIG. 3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

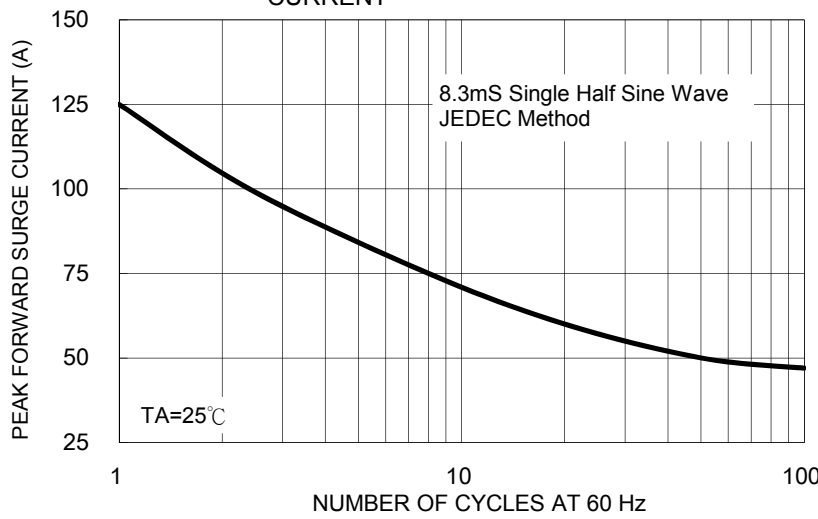


FIG. 5- TYPICAL FORWARD CHARACTERISTICS

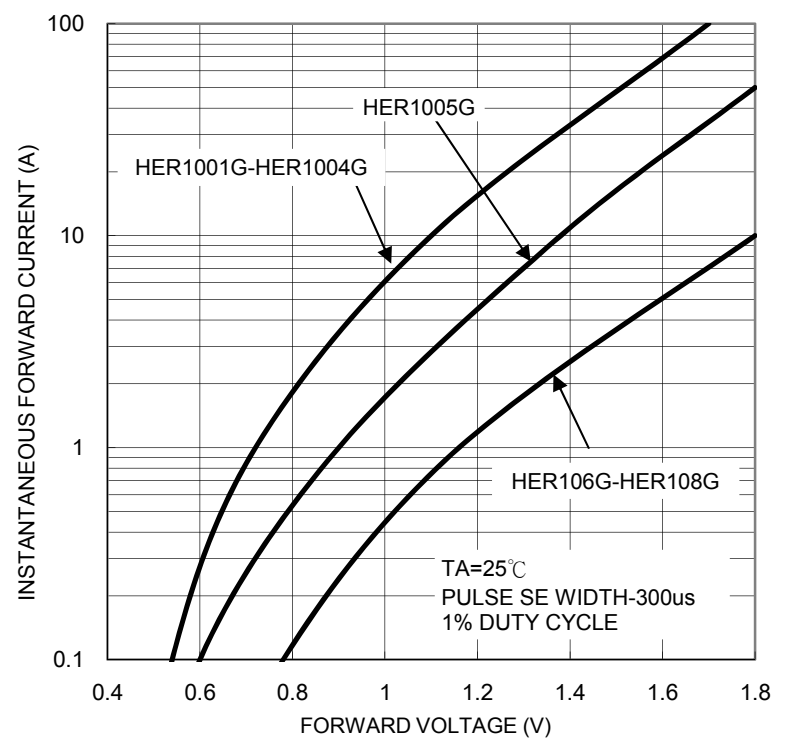


FIG. 4- TYPICAL JUNCTION CAPACITANCE

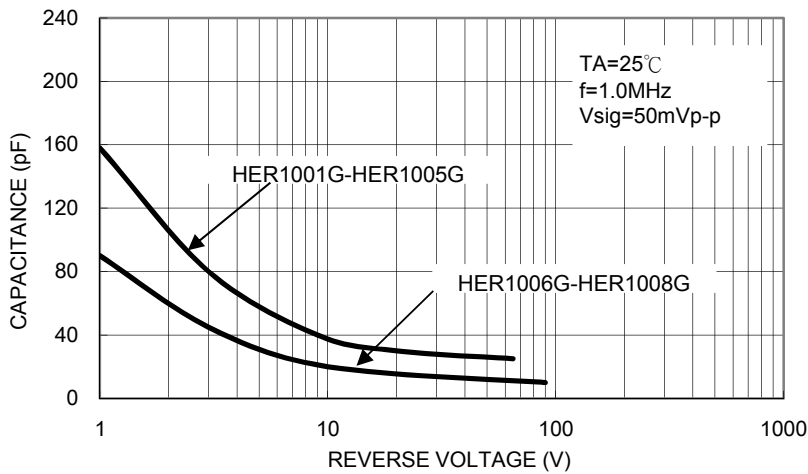
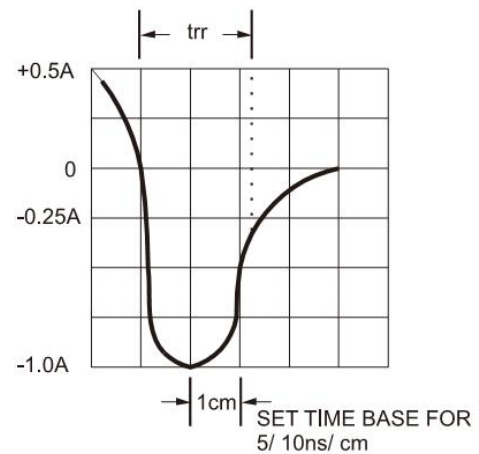
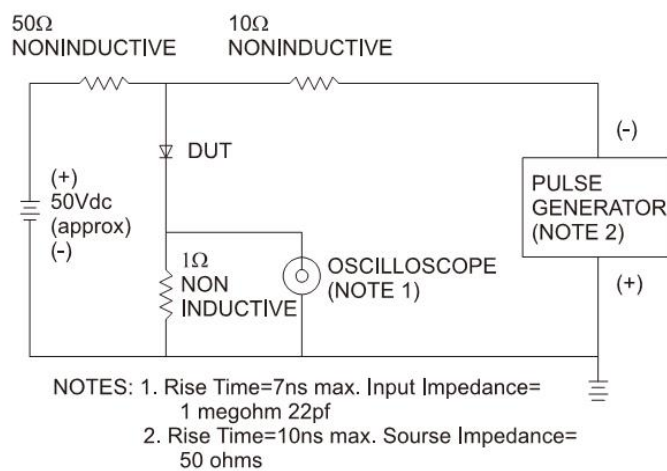


FIG. 6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

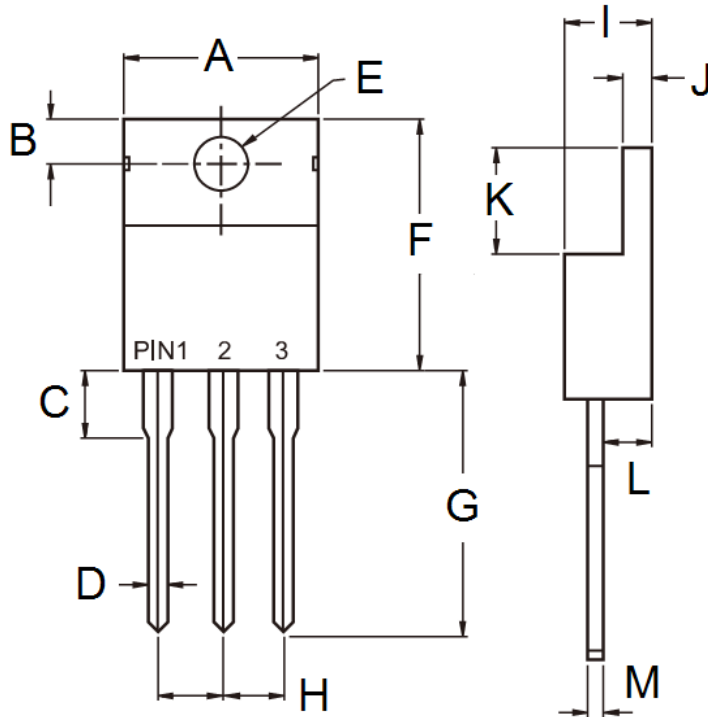


Ordering information

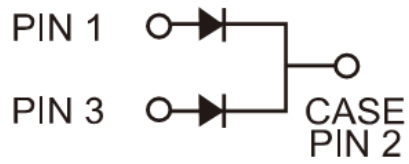
Part No.	Package	BULK Packing	Packing code	Packing code (Green)
HER100xG	TO-220AB	50 / TUBE	C0	C0G

Note: "x" is Device Code from "1" thru "8".

Dimensions



DIM.	Unit(mm)		Unit(inch)	
	Min	Max	Min	Max
A	-	10.50	-	0.413
B	2.62	3.44	0.103	0.135
C	2.80	4.20	0.110	0.165
D	0.68	0.94	0.027	0.037
E	3.54	4.00	0.139	0.157
F	14.60	16.00	0.575	0.630
G	13.19	14.79	0.519	0.582
H	2.41	2.67	0.095	0.105
I	4.42	4.76	0.174	0.187
J	1.14	1.40	0.045	0.055
K	5.84	6.86	0.230	0.270
L	2.20	2.80	0.087	0.110
M	0.35	0.64	0.014	0.025



Marking Diagram



- P/N = Specific Device Code
- G = Green Compound
- YWW = Date Code
- F = Factory Code

Mouser Electronics

Authorized Distributor

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